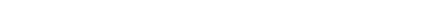


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				Filing Date	January 16, 1998
				First Named Inventor	Joseph W. Lyding et al.
				Group Art Unit	1763
				Examiner Name	Unknown
Sheet	1	of	2	Attorney Docket Number	22010-128/IL-2-CON

Examiner Signature		Date Considered	7/21/99
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First Named Inventor	Joseph W. Lyding et al.
Group Art Unit	1763
Examiner Name	Unknown
Attorney Docket Number	22010-128/IL-2-CON

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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials ¹	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Lee		GANGULY, Gautam and MATSUDA, Akihisa, "Light-Induced Defect Densities in Hydrogenated and Deuterated Amorphous Silicon Deposited at Different Substrate Temperatures", <u>The Amer. Physical Soc.</u> , Vol. 49, No. 16, pp. 10-986-10 990, (April 15, 1994).	
Lee		MIKKELSEN, J.C., Jr., "Secondary Ion Mass Spectrometry Characterization of D ₂ O and H ₂ ¹⁸ O Steam Oxidation of Silicon", <u>J. of Electronic Matl's</u> , Vol. 11, No. 3, pp. 541-558, (1982).	
Lee		MYERS, S.M. and RICHARDS, P.M., "Interactions of Deuterium With Ion-Irradiated SiO ₂ on Si", <u>J. Appl. Phys.</u> , Vol. 67, No. 9, pp. 4064-4071 (May 1, 1990).	
Lee		PARK, Heungsoo and HELMS, C.R., "The Effect of Annealing Treatment on the Distribution of Deuterium in Silicon and in Silicon/Silicon Oxide Systems", <u>J. Electrochem. Soc.</u> , Vol. 139, No. 7, pp. 2042-2046 (July 1992).	
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